MOSFETs Silicon N-Channel MOS

SSM3K62TU

1. Applications

- Power Management Switches
- DC-DC Converters

2. Features

(1) AEC-Q101 qualified

(2) 1.2-V drive

(3) Low drain-source on-resistance

: $R_{DS(ON)}$ = 43 mΩ (typ.) (@V_{GS} = 4.5 V)

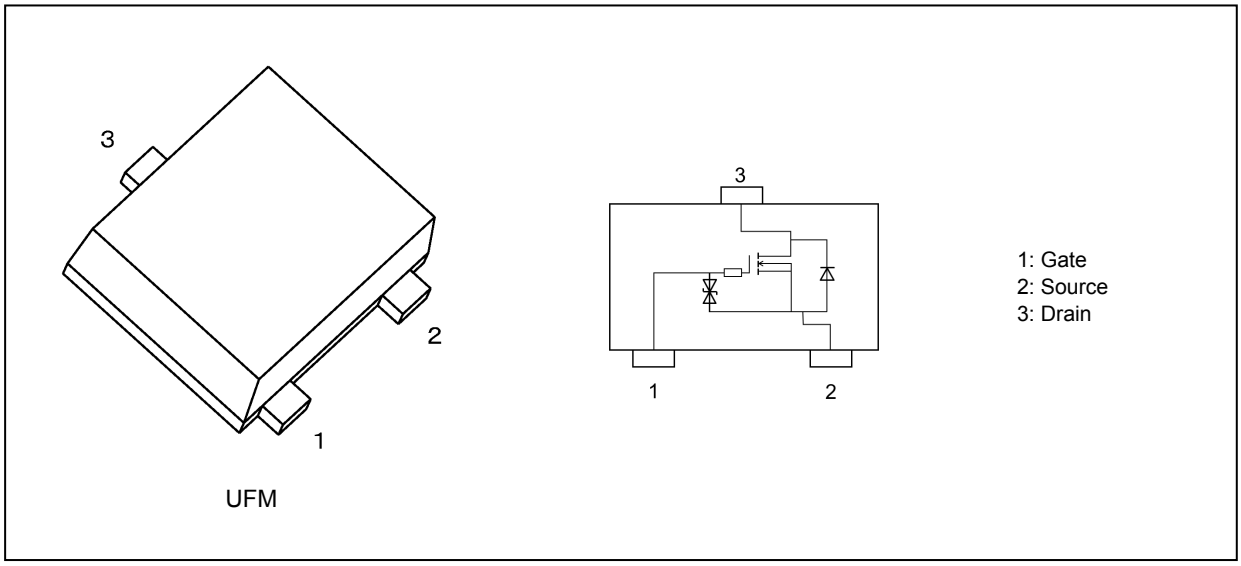
$R_{DS(ON)}$ = 50 mΩ (typ.) (@V_{GS} = 2.5 V)

$R_{DS(ON)}$ = 60 mΩ (typ.) (@V_{GS} = 1.8 V)

$R_{DS(ON)}$ = 70 mΩ (typ.) (@V_{GS} = 1.5 V)

$R_{DS(ON)}$ = 98 mΩ (typ.) (@V_{GS} = 1.2 V)

3. Packaging and Pin Assignment



Start of commercial production
2016-08

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4. Absolute Maximum Ratings (Note) (Unless otherwise specified, T_a = 25 °C)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	20	V
Gate-source voltage			V_{GSS}	±8	
Drain current (DC)		(Note 1)	I_D	0.8	A
Drain current (pulsed)		(Note 1), (Note 2)	I_{DP}	1.6	
Power dissipation		(Note 3)	P_D	500	mW
Power dissipation	(t < 1s)	(Note 3)	P_D	1000	mW
Channel temperature			T_{ch}	150	°C
Storage temperature			T_{stg}	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Pulse width (PW) ≤ 10 ms, duty ≤ 1%

Note 3: Device mounted on an FR4 board. (FR4, 25.4 mm × 25.4 mm × 1.6 mm, Cu pad: 645 mm^2)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, $R_{th(ch-a)}$, and the drain power dissipation, P_D, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

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5. Electrical Characteristics

5.1. Static Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{DS} = 0 V, V_{GS} = ±8 V	—	—	±10	μA
Drain cut-off current		I_{DSS}	V_{DS} = 10 V, V_{GS} = 0 V	—	—	1	
Drain-source breakdown voltage		$V_{(BR)DSS}$	I_D = 1 mA, V_{GS} = 0 V	20	—	—	V
Drain-source breakdown voltage	(Note 1)	$V_{(BR)DSX}$	I_D = 1 mA, V_{GS} = -5 V	15	—	—	
Gate threshold voltage	(Note 2)	V_{th}	V_{DS} = 3 V, I_D = 1 mA	0.4	0.6	1.0	
Drain-source on-resistance	(Note 3)	$R_{DS(ON)}$	I_D = 100 mA, V_{GS} = 1.2 V	—	98	432	mΩ
			I_D = 200 mA, V_{GS} = 1.5 V	—	70	139	
			I_D = 600 mA, V_{GS} = 1.8 V	—	60	89	
			I_D = 800 mA, V_{GS} = 2.5 V	—	50	68	
			I_D = 800 mA, V_{GS} = 4.5 V	—	43	57	
Forward transfer admittance	(Note 3)	$\|Y_{fs}\|$	V_{DS} = 3 V, I_D = 200 mA	—	3.0	—	S

Note 1: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (1 mA for this device). Then, for normal switching operation, $V_{GS(ON)}$ must be higher than V_{th}, and $V_{GS(OFF)}$ must be lower than V_{th}. This relationship can be expressed as: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$.
Take this into consideration when using the device.

Note 3: Pulse measurement.

5.2. Dynamic Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	—	177	—	pF
Reverse transfer capacitance	C_{rss}		—	17	—	
Output capacitance	C_{oss}		—	52	—	
Switching time (turn-on time)	t_{on}	V_{DD} = 10 V, I_D = 800 mA, V_{GS} = 0 to 4.5 V, R_G = 50 Ω	—	332	—	ns
Switching time (turn-off time)	t_{off}		—	2653	—	

5.3. Switching Time Test Circuit

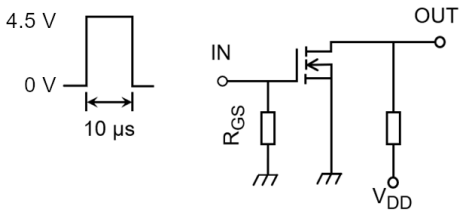

Fig. 5.3.1 Switching Time Test Circuit

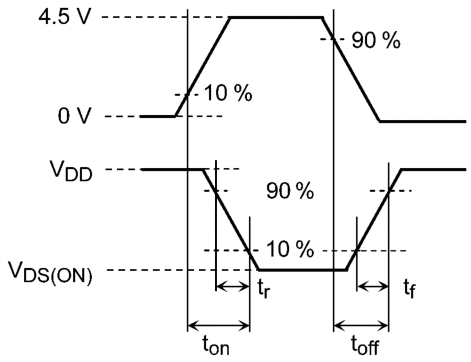

Fig. 5.3.2 Input Waveform/Output Waveform

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5.4. Gate Charge Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	V_{DD} = 10 V, I_D = 800 mA, V_{GS} = 4.5 V	—	2.0	—	nC
Gate-source charge 1	Q_{gs1}		—	1.3	—	
Gate-drain charge	Q_{gd}		—	0.6	—	

5.5. Source-Drain Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Diode forward voltage	(Note 1)	V_{DSF}	I_D = -800 mA, V_{GS} = 0 V	—	-0.6	-1.2	V

Note 1: Pulse measurement.

6. Marking

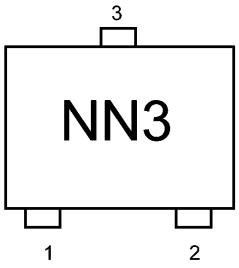

Fig. 6.1 Marking

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7. Characteristics Curves (Note)

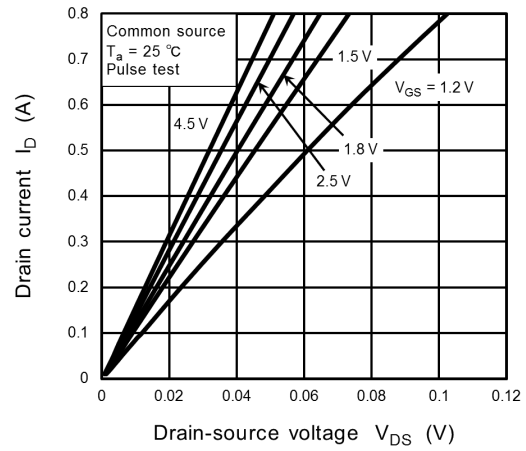

Fig. 7.1 I_D - V_{DS}

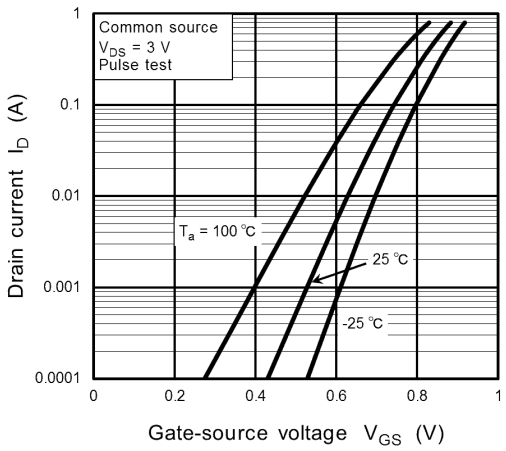

Fig. 7.2 I_D - V_{GS}

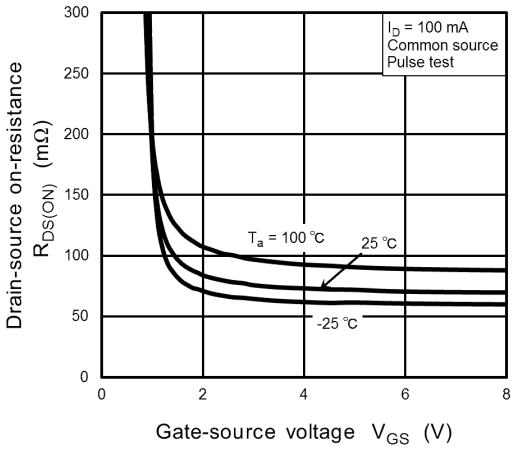

Fig. 7.3 $R_{DS(ON)}$ - V_{GS}

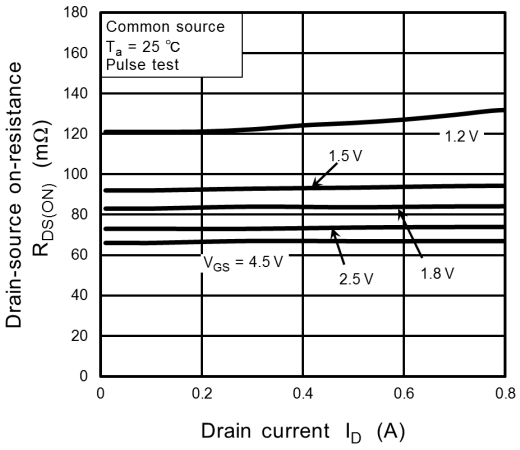

Fig. 7.4 $R_{DS(ON)}$ - I_D

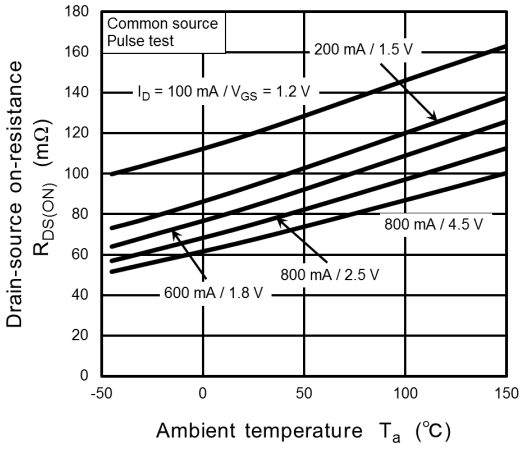

Fig. 7.5 $R_{DS(ON)}$ - T_a

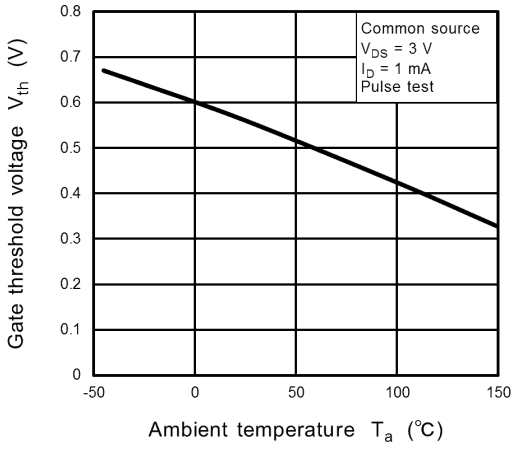

Fig. 7.6 V_{th} - T_a

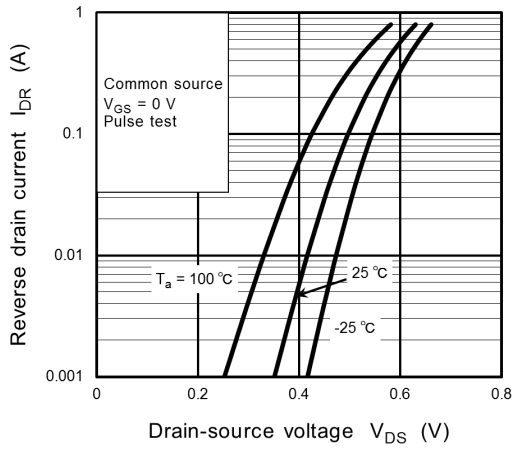

Fig. 7.7 I_{DR} - V_{DS}

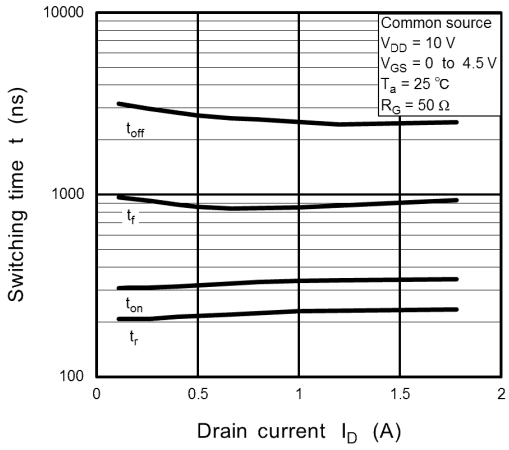

Fig. 7.8 t - I_D

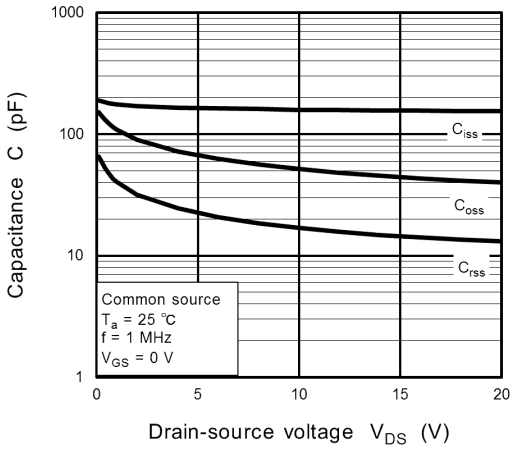

Fig. 7.9 C - V_{DS}

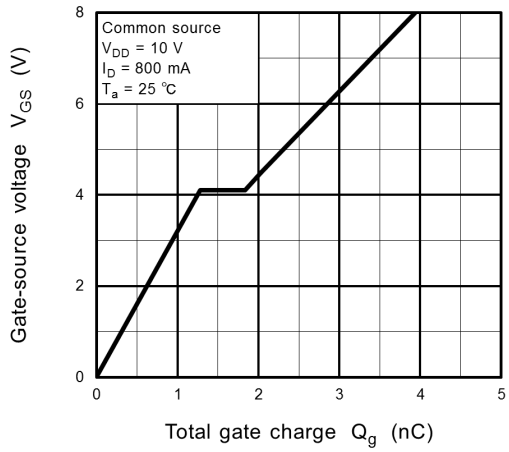

Fig. 7.10 Dynamic Input Characteristics

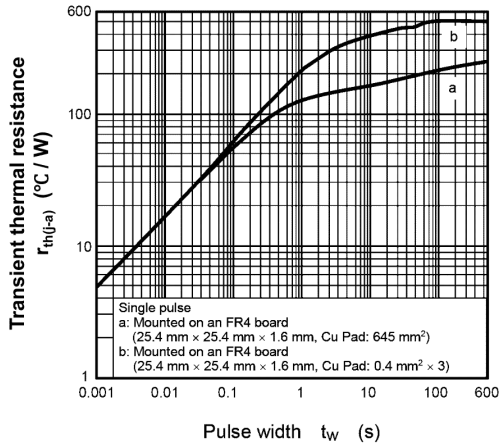

Fig. 7.11 r_{th} - t_w

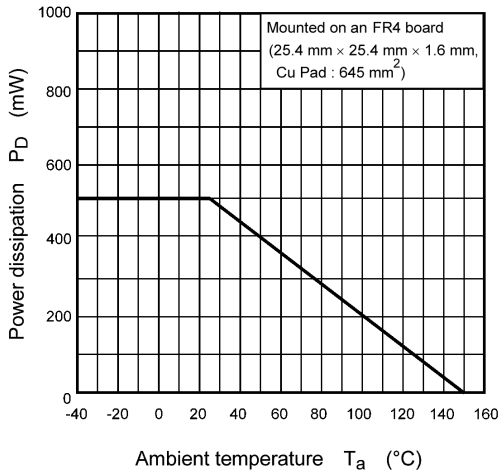

Fig. 7.12 P_D - T_a

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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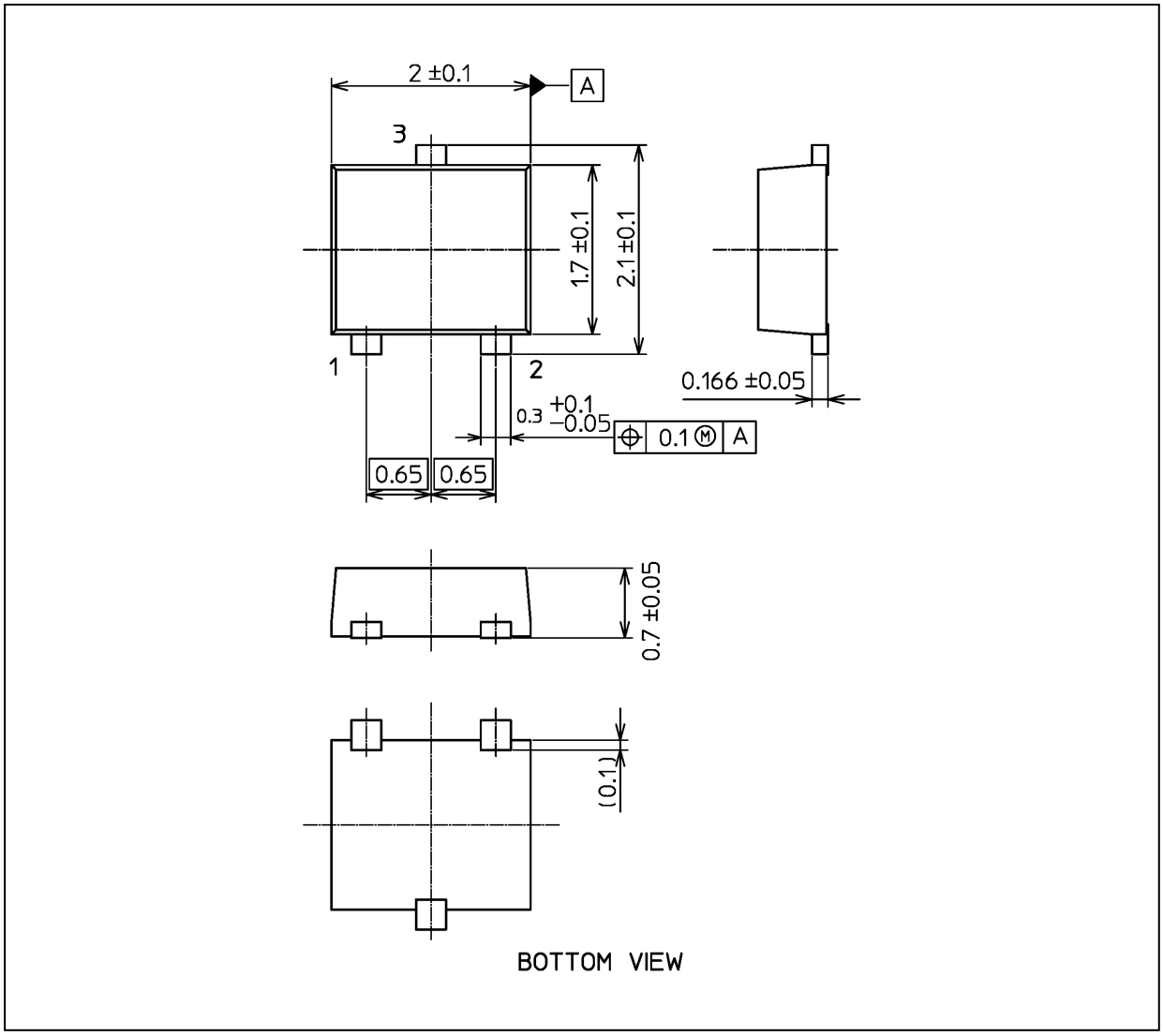
Package Dimensions

Unit: mm



Weight: 6.6 mg (typ.)

Package Name(s)
Nickname: UFM

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